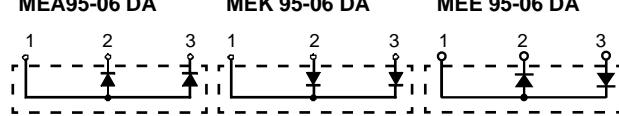


Fast Recovery Epitaxial Diode (FRED) Module

**MEA 95-06 DA
MEK 95-06 DA
MEE 95-06 DA**

**$V_{RRM} = 600 \text{ V}$
 $I_{FAV} = 95 \text{ A}$
 $t_{rr} = 250 \text{ ns}$**

V_{RSM}	V_{RRM}	Type	MEA95-06 DA	MEK 95-06 DA	MEE 95-06 DA
600	600		1 2 3	1 2 3	1 2 3



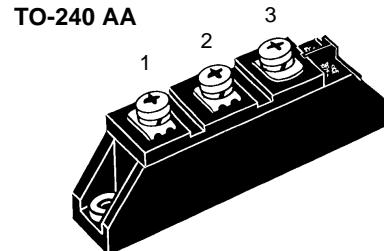
Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}	$T_{case} = 75^\circ\text{C}$	142	A
I_{FAV}^*	$T_{case} = 75^\circ\text{C}$; rectangular, $d = 0.5$	95	A
I_{FRM}	$t_p < 10 \mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	TBD	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1200	A
		1300	A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1080	A
		1170	A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	7200	A^2s
		7100	A^2s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	5800	A^2s
		5700	A^2s
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{sig}		-40...+125	$^\circ\text{C}$
T_{Hmax}		110	$^\circ\text{C}$
P_{tot}	$T_{case} = 25^\circ\text{C}$	280	W
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000	V_\sim
		3600	V_\sim
M_d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4/22-35 Nm/lb.in.	
		2.5-4/22-35 Nm/lb.in.	
d_s	Creep distance on surface	12.7	mm
d_a	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s^2
Weight		90	g

Symbol	Test Conditions	Characteristic Values (per diode) typ. max.	
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	2 0.5 34	mA
V_F	$I_F = 100 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$ $I_F = 300 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.36 1.55 2.05 2.09	V
V_{TO}	For power-loss calculations only	1.01	V
r_T	$T_{VJ} = T_{VJM}$	2.85	$\text{m}\Omega$
R_{thJH}	DC current	0.550	K/W
R_{thJC}	DC current	0.450	K/W
t_{rr}	$I_F = 100 \text{ A}$ $V_R = 300 \text{ V}$ $-di/dt = 200 \text{ A}/\mu\text{s}$	250	ns
I_{RM}	$T_{VJ} = 100^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 100^\circ\text{C}$	300 14 21	A

* I_{FAV} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.6 V_{RRM}$, duty cycle $d = 0.5$

Data according to DIN/IEC 747

IXYS reserves the right to change limits, test conditions and dimensions



Features

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- Isolation voltage 3600 V
- UL registered E 72873

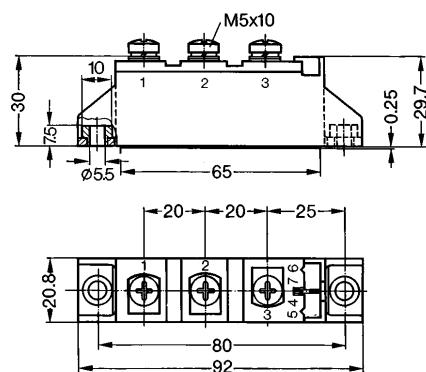
Applications

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions in mm (1 mm = 0.0394")



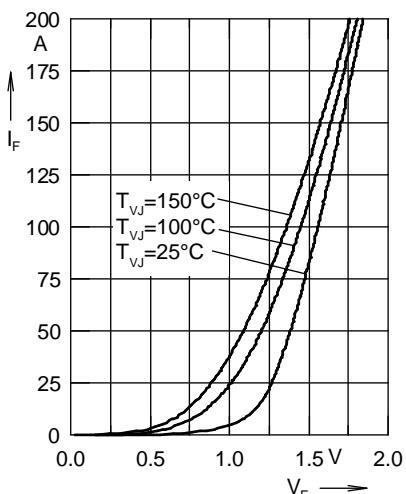


Fig. 1 Forward current I_F versus voltage drop V_F per leg

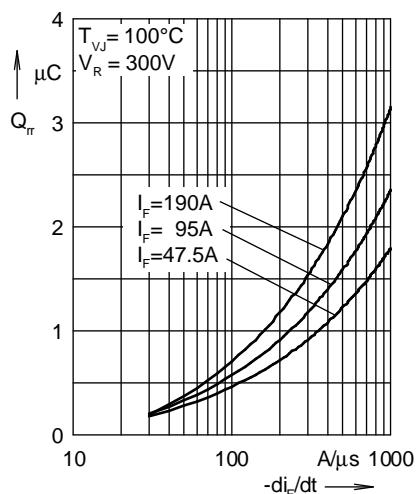


Fig. 2 Reverse recovery charge Q_{rr} versus $-di_F/dt$

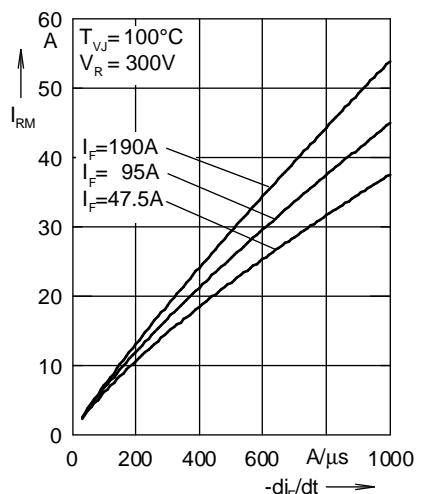


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

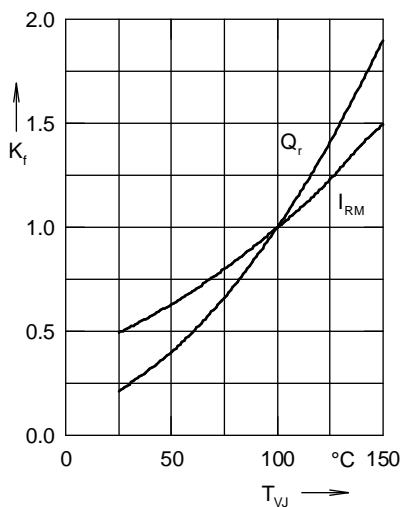


Fig. 4 Dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

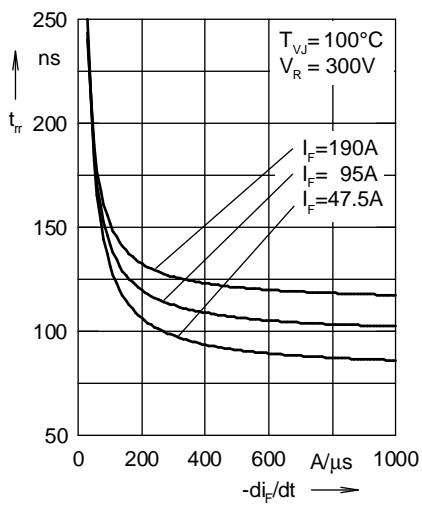


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$